In th Claims

Claims 1-24 (Canceled).

25. (Currently Amended): A process of forming MRAM circuitry, comprising:

forming an MRAM cell comprising magnetic material over a substrate; chemical vapor depositing a silicon carbide comprising layer over the MRAM cell at a temperature of no greater than 500°C;

forming an insulative material over the silicon carbide comprising layer;

etching a contact opening through the insulative material using the silicon carbide comprising layer as an etch stop; and

plasma etching within the contact opening through the silicon carbide comprising layer using a gas chemistry comprising oxygen and hydrogen to extend the contact opening through the silicon carbide comprising layer to the magnetic material of the MRAM cell, and under conditions which etches etch the silicon carbide comprising layer at a rate at least twice that of any etching of the insulative material.

- 26. (Original): The method of claim 25 wherein the MRAM cell comprises a dielectric layer sandwiched between magnetic material layers.
- 27. (Original): The method of claim 25 wherein the insulative material comprises SiO₂.

- 28. (Original): The method of claim 25 comprising conducting the chemical vapor depositing at a temperature of no greater than 200°C.
- 29. (Original): The method of claim 25 wherein the substrate is not exposed to a temperature greater than 500°C between the depositing and the etching.
- 30. (Original): The method of claim 25 wherein the substrate is not exposed to a temperature greater than the highest temperature during the depositing between the depositing and the etching.
- 31. (Original): The method of claim 25 comprising conducting the chemical vapor depositing at a temperature of no greater than 250°C, and wherein the substrate is not exposed to a temperature greater than 250°C between the depositing and the etching.
- 32. (Original): The method of claim 25 wherein the oxygen is derived from the group consisting of O_2 , O_3 , NO_x , CO, CO_2 , and mixtures thereof.
- 33. (Original): The method of claim 25 wherein the hydrogen is derived from the group consisting of H₂, NH₃, CH₄, and mixtures thereof.

- 34. (Original): The method of claim 25 wherein the plasma etching is conducted within a chamber, plasma during the plasma etching being first formed within the chamber.
- 35. (Original): The method of claim 25 comprising after the plasma etching, forming conductive material within the contact opening.

Claims 36-47 (Canceled).

- 48. (New): The method of claim 25 wherein the chemical vapor depositing is plasma enhanced.
 - 49. (New): The method of claim 25 wherein,

the oxygen is derived from the group consisting of O_2 , O_3 , NO_x , CO, CO_2 , and mixtures thereof; and

the hydrogen is derived from the group consisting of H_2 , NH_3 , CH_4 , and mixtures thereof.

50. (New): The method of claim 25 wherein the oxygen is derived at least in part from O_2 and the hydrogen is derived at least in part from NH_3 .

- 51. (New): The method of claim 25 wherein the plasma etching is conducted within a chamber, plasma during the plasma etching being first formed remote from the chamber.
- 52. (New): The method of claim 25 comprising plasma etching under conditions which etch the silicon carbide comprising layer at a rate at least three times that of any etching of the insulative material.
- 53. (New): The method of claim 25 comprising plasma etching under conditions which etch the silicon carbide comprising layer at a rate at least four times that of any etching of the insulative material.
- 54. (New): The method of claim 25 wherein the oxygen is derived from a gas comprising O_2 .
- 55. (New): The method of claim 25 wherein the oxygen is derived from a gas comprising O_3 .
- 56. (New): The method of claim 25 wherein the oxygen is derived from a gas comprising NO_x .
- 57. (New): The method of claim 25 wherein the oxygen is derived from a gas comprising CO.

- 58. (New): The method of claim 25 wherein the oxygen is derived from a gas comprising CO₂.
- 59. (New): The method of claim 25 wherein the hydrogen is derived from a gas comprising H_2 .
- 60. (New): The method of claim 25 wherein the hydrogen is derived from a gas comprising NH_3 .
- 61. (New): The method of claim 25 wherein the hydrogen is derived from a gas comprising CH₄.